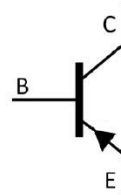


Power Amplifier Applications

- ① Complementary to 2SC4793
- ② High collector voltage: $V_{CEO} = -230V$ (min)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the Absolute maximum ratings.



PIN1 : Base
PIN 2 : Collector
PIN 3 : Emitter

Absolute Maximum (°C):

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-230	V
Collector-emitter voltage	V_{CEO}	-230	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-1	A
Base current	I_B	-0.2	A
Collector power dissipation (Tc=25°C)	P_C	50	W
Junction temperature	T_j	150	°C
Storage temperature range	T_{STG}	-55~150	°C

Thermal Characteristics

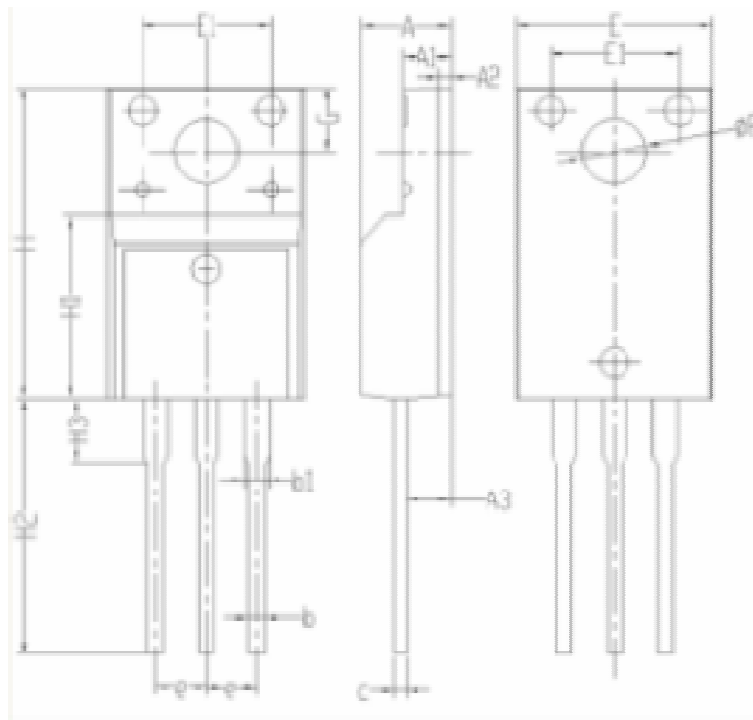
Symbol	Parameter	Typ	Units
$R_{\theta jc}$	Junction-to-Case	3.0	°C/W

Electrical Characteristics (°C):

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Cut-off Current	I_{CBO}	$V_{CB}=-230V, I_E=0$			-1.0	μA
Emitter-Base Cut-off Current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-1.0	μA
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_C=-1mA$	-230			V
DC current gain	h_{FE}	$I_C=-0.1A; V_{CE}=-5V$	100		300	
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-0.5A; I_B=-0.05A$			-0.5	V
Base-Emitter Saturation Voltage	V_{BEsat}	$I_C=-0.5A, I_B=-0.05A$			-1.4	V
Base-emitter voltage	V_{BE}	$V_{CE}=-5V; I_C=-0.5A$			-1.5	V
Transition frequency	f_T	$V_{CE}=-10V; I_C=-100mA$		40		MHz

Package Information

TO-220F PACKAGE



Symbol	Dimensions (millimeters)	
	Min	Max
A	4.35	4.75
A1	2.30	2.70
A2	0.40	0.80
A3	2.10	2.50
b	0.60	1.00
b1	1.00	1.40
c	0.30	0.70
e	2.30	2.70
E	9.80	10.2
E1	6.30	6.70
H	15.6	16.0
H1	8.80	9.20
H2	12.9	13.5
H3	3.10	3.50
G	3.10	3.50
ϕP	3.10	3.50